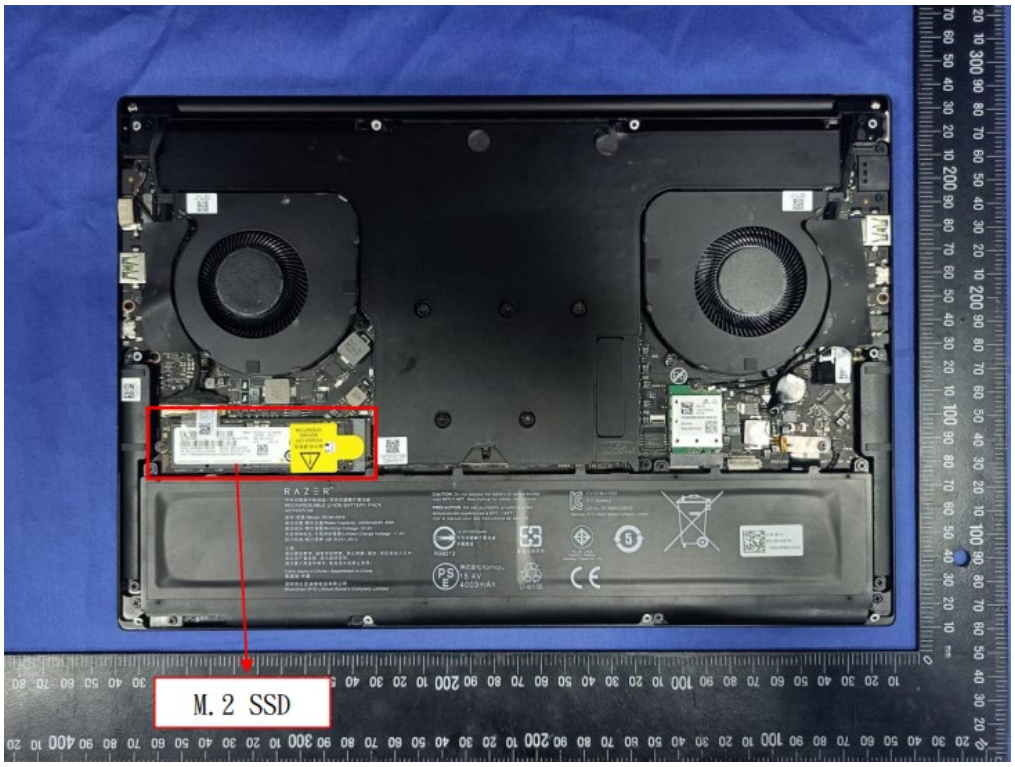
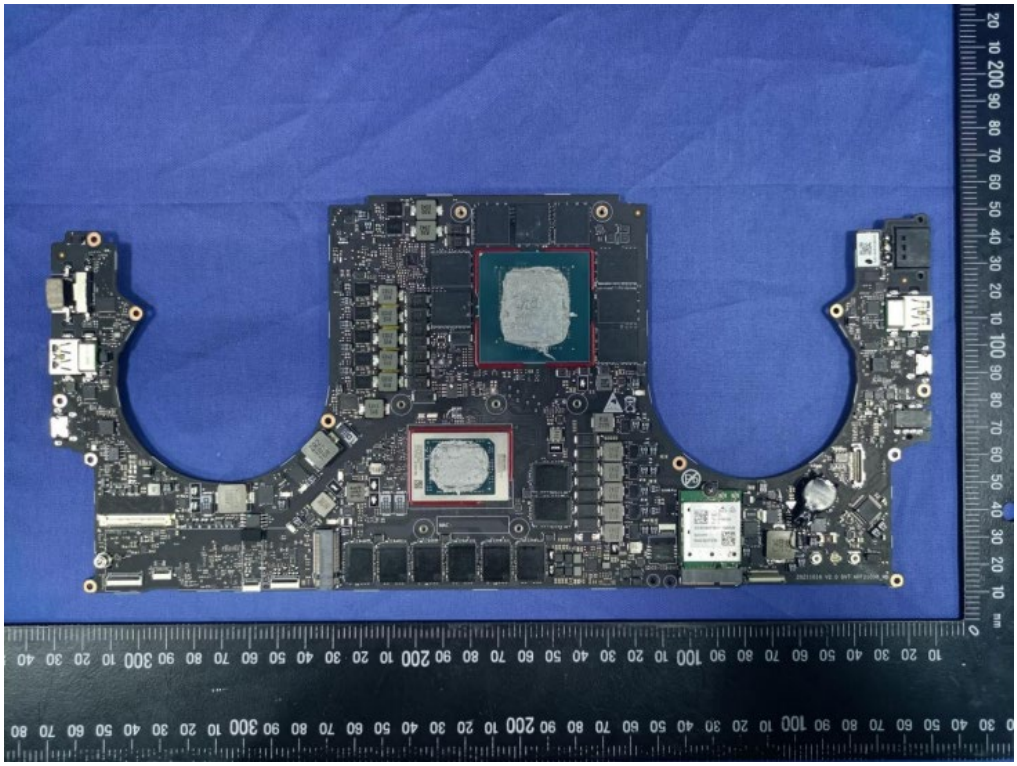
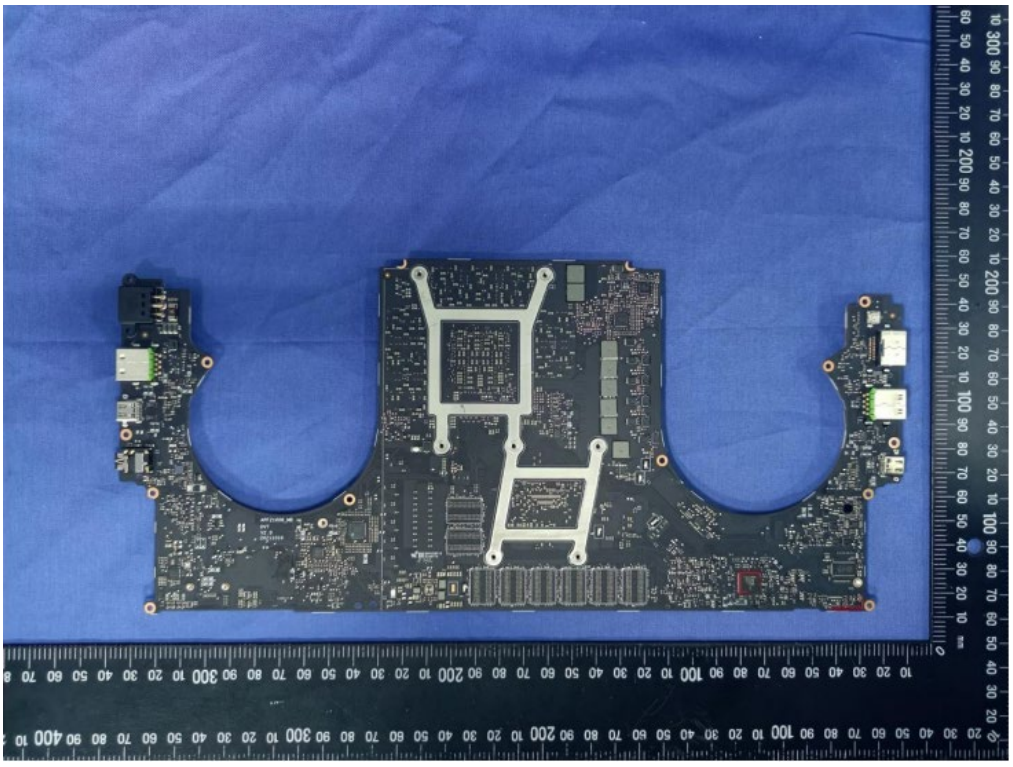


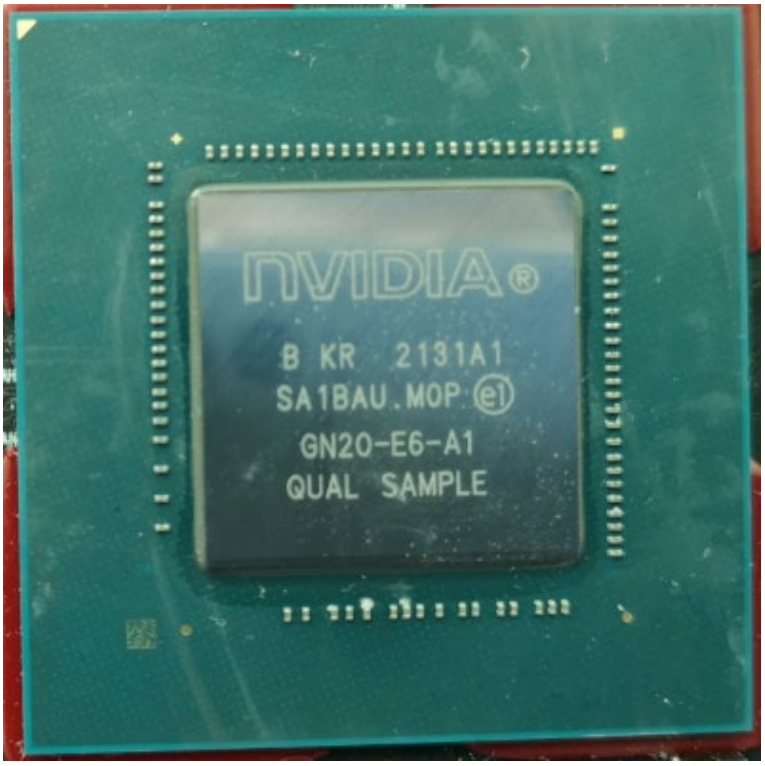

M. 2 SSD

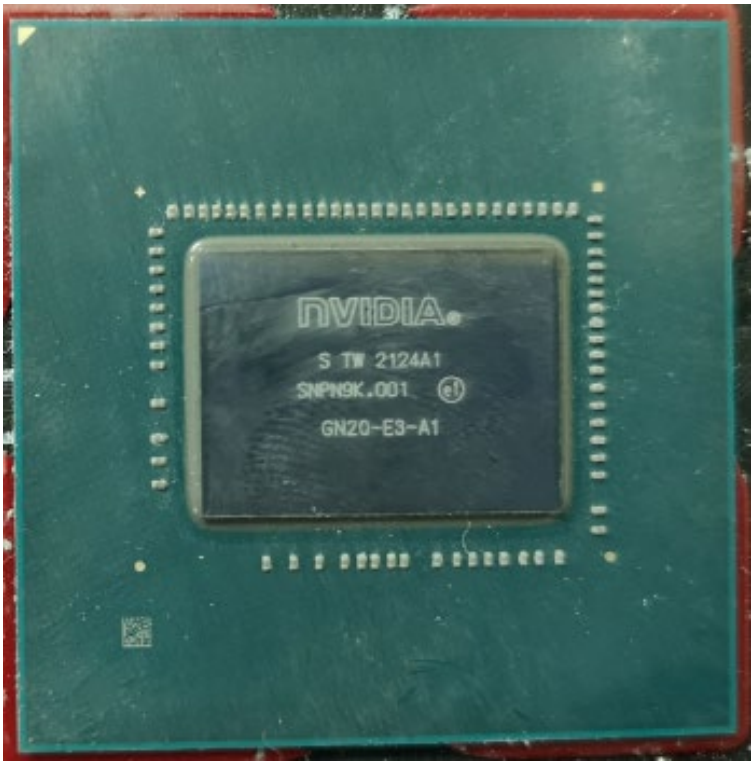


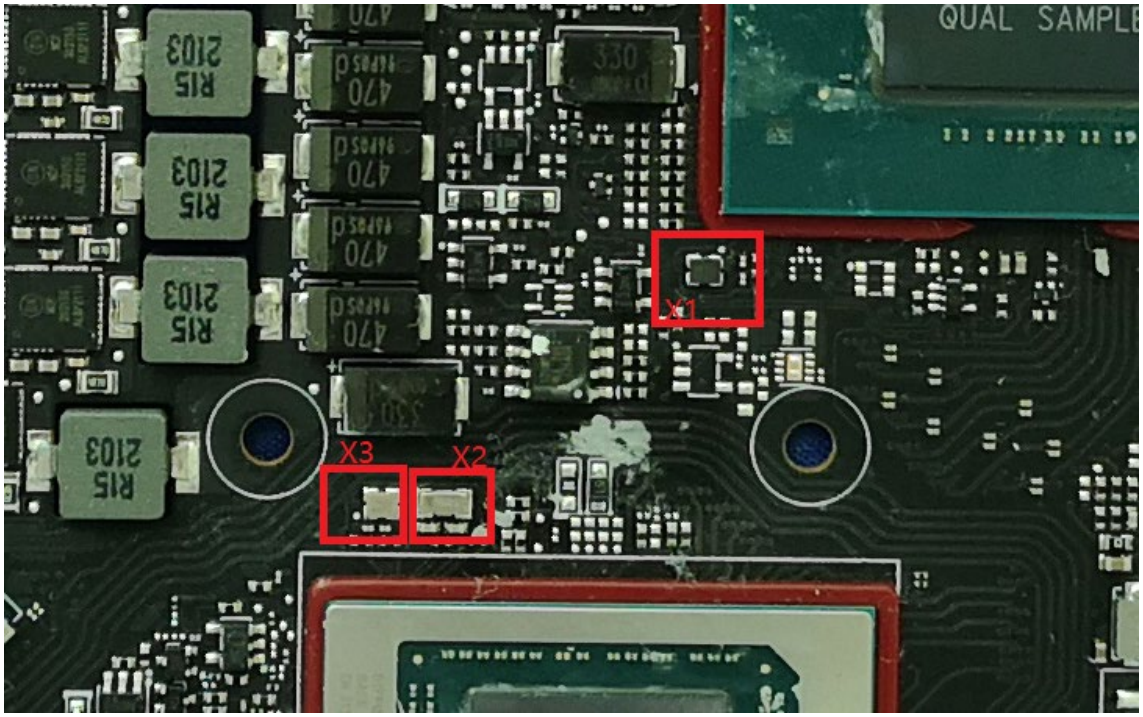


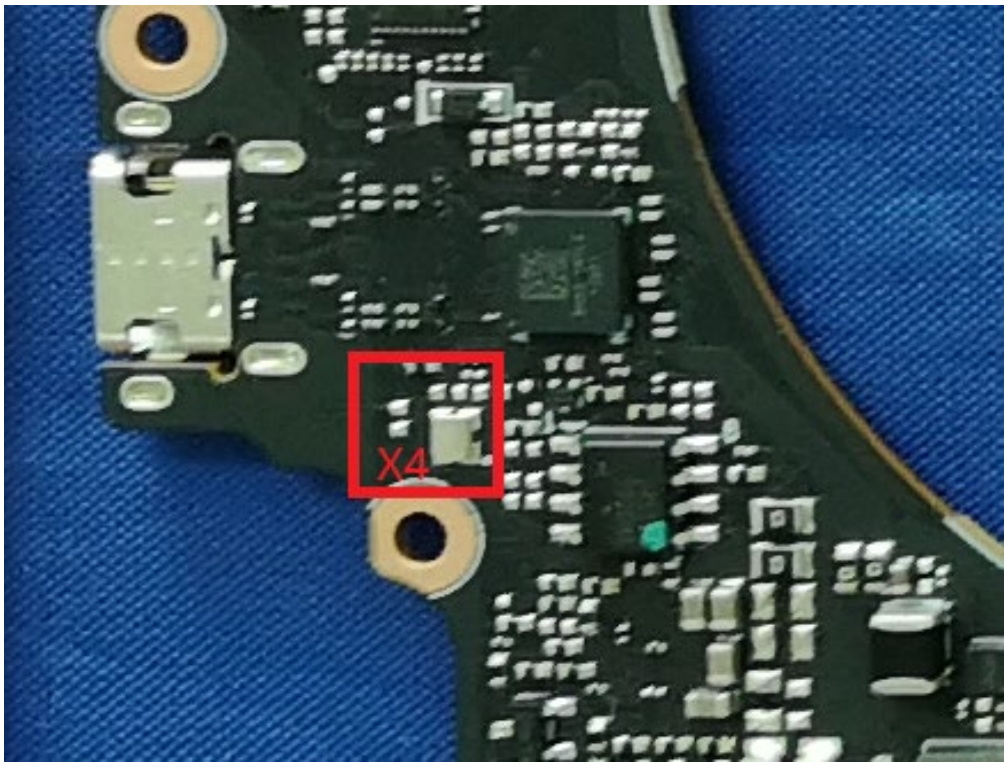


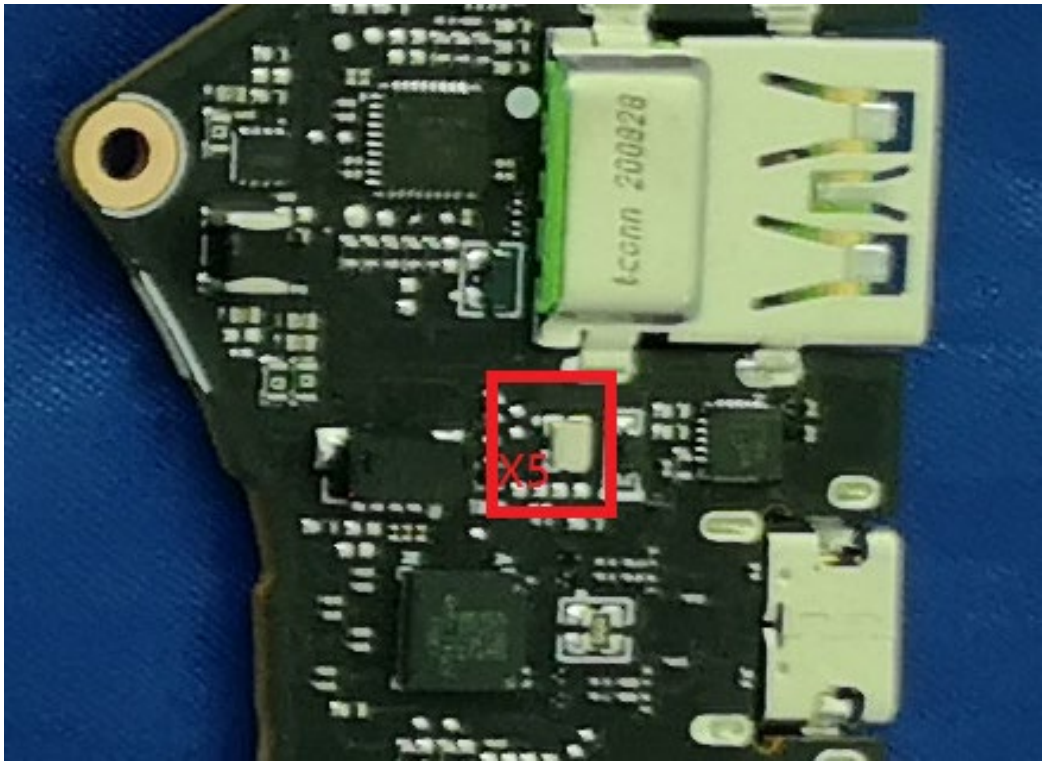

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SNZHFV.000
GN20-E8-A1
QUAL SAMPLE


NVIDIA
B KR 2131A1
SA1BAU.M0P
GN20-E6-A1
QUAL SAMPLE


NVIDIA
S TW 2124A1
SNPN9K.001
GN20-E3-A1


X1
X2
X3

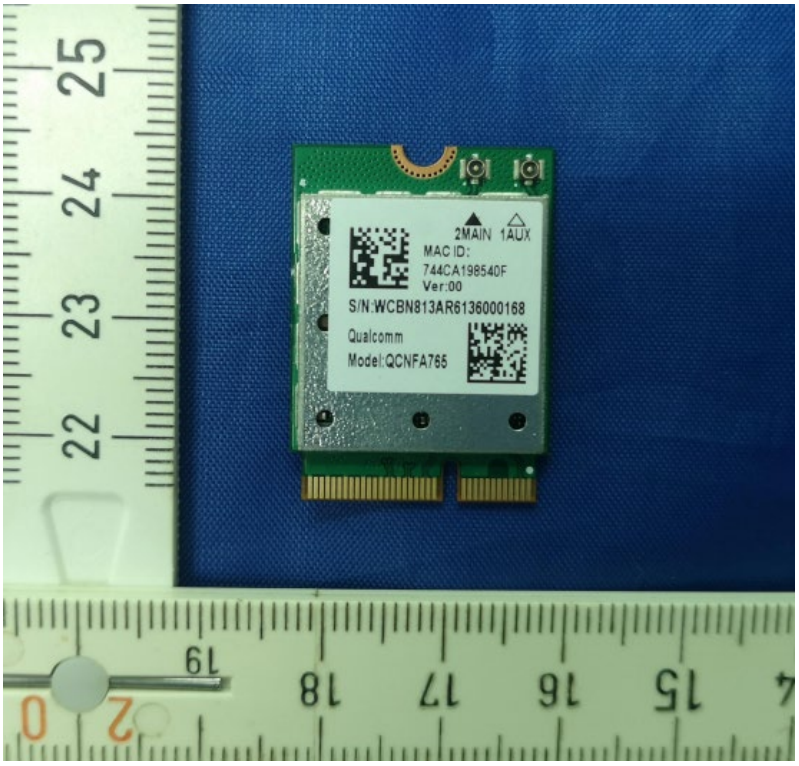

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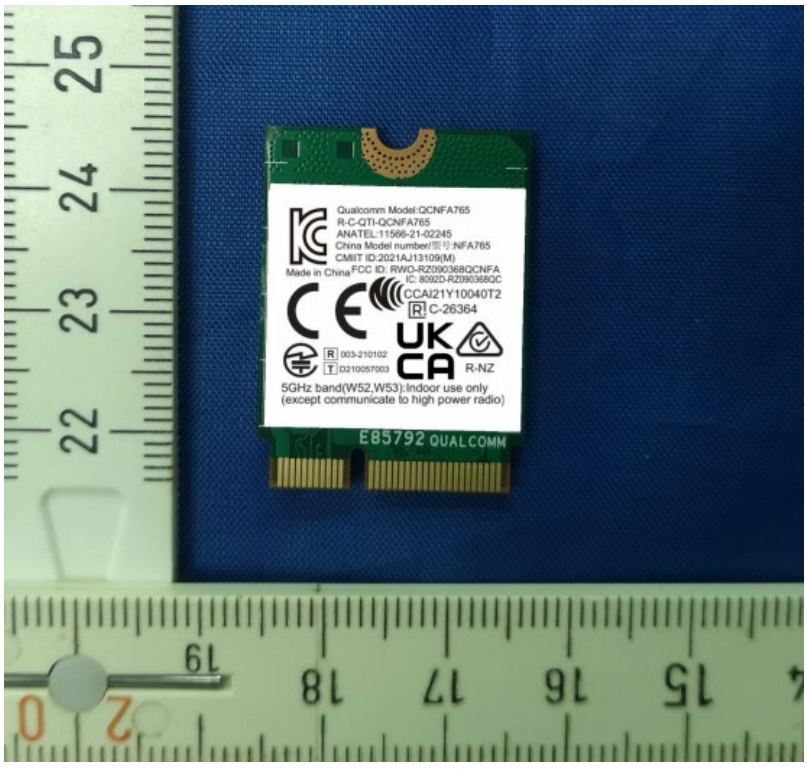

X5





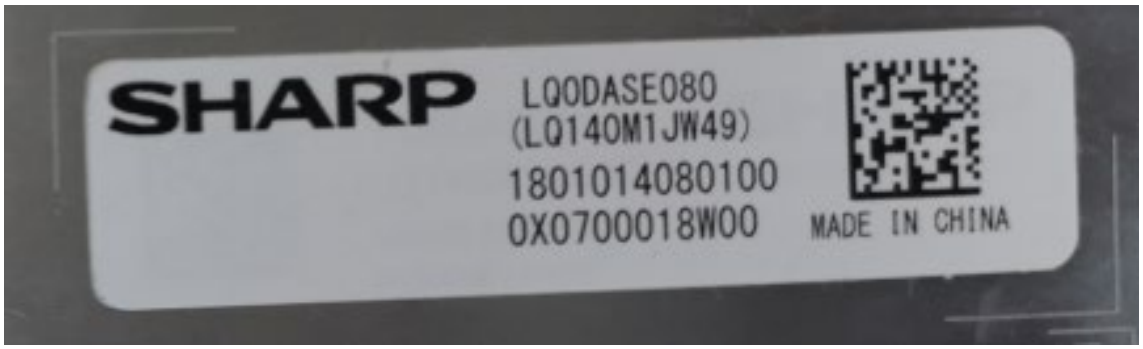

RAZER
可充式锂离子电池组 / 可充式鋰離子電池組
RECHARGEABLE LI-ION BATTERY PACK
4ICP4/47/140
型号/型號/Model: RC30-0370
额定容量/額定容量/Rated Capacity: 4003mAh/61.6Wh
额定电压/額定電壓/Nominal Voltage: 15.4V
充电限制电压/充電限制電壓/Limited Charge Voltage: 17.6V
执行标准/執行標準: GB 31241-2014
注意：
電池警告事項，請參考說明書。禁止拆解、撞击，挤压或投入火中。
若出现严重鼓胀，请勿继续使用。
请勿置于高温环境中，电池浸水后禁止使用！
Cells made in China / Assembled in China
製造地: 中國
深圳市比亚迪锂电池有限公司
ShenZhen BYD Lithium Battery Company Limited
CAUTION Do not expose the battery to temperatures over 65°C/149°F. See manual for safety instructions.
PRÉCAUTION Ne pas soumettre la batterie à des temperatures supérieures à 65°C (149°F). Voir le manuel pour des instructions de sécurité.
15.4V/4003mAh
可充式鋰離子電池組
中国製造
R39212
廢電池請回收
株式会社Komoju
15.4V
4003mAh
Li-ion 00
YUXXXXX-XXXXX
전지(Battery)
A/S No.:0079885238003
Shenzhen BYD Lithium Battery Company Limited
TIS: 2217-2548
Imported by Ellegoo(s) Technology (Thailand) CO., LTD.
CE

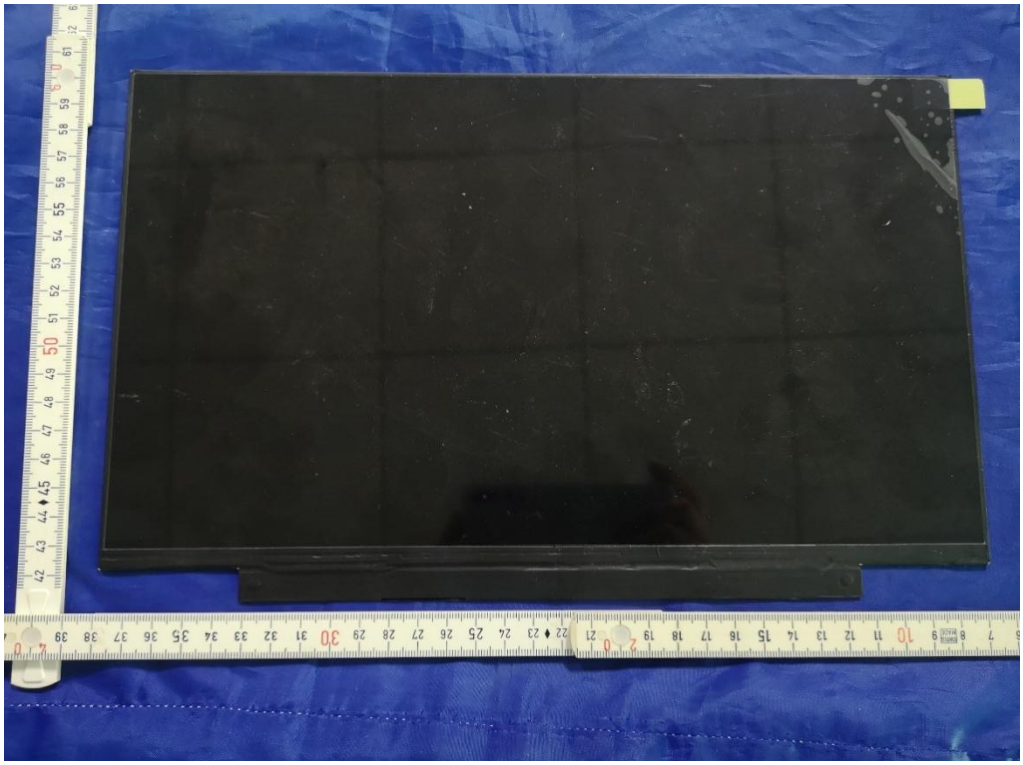

2MAIN 1AUX
MAC ID:
744CA198540F
Ver:00
S/N:WCBN813AR6136000168
Qualcomm
Model:QCNFA765


Qualcomm Model:QCNFA765
R-C-QTI-QCNFA765
ANATEL:11566-21-02245
China Model number/型号:NFA765
CMIIT ID:2021AJ13109(M)
Made in China FCC ID: RWO-RZ090368QCNFA
IC: 8592D-RZ090368QC
CCAI21Y10040T2
C-26364
003-210102
D210057003
R-NZ
5GHz band(W52,W53):Indoor use only
(except communicate to high power radio)
E85792 QUALCOMM




SHARP


SHARP
LQ0DASE080
(LQ140M1JW49)
1801014080100
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MADE IN CHINA



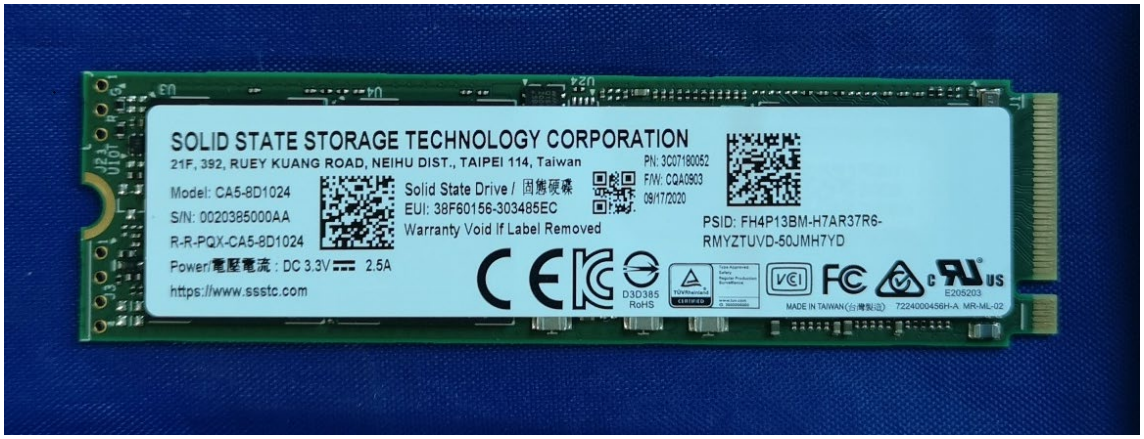



18010-14070500-20082100343
LM140LF1F
02
NJF0108MN82104811
EDID: 01
PANDA
RoHS
Made In China



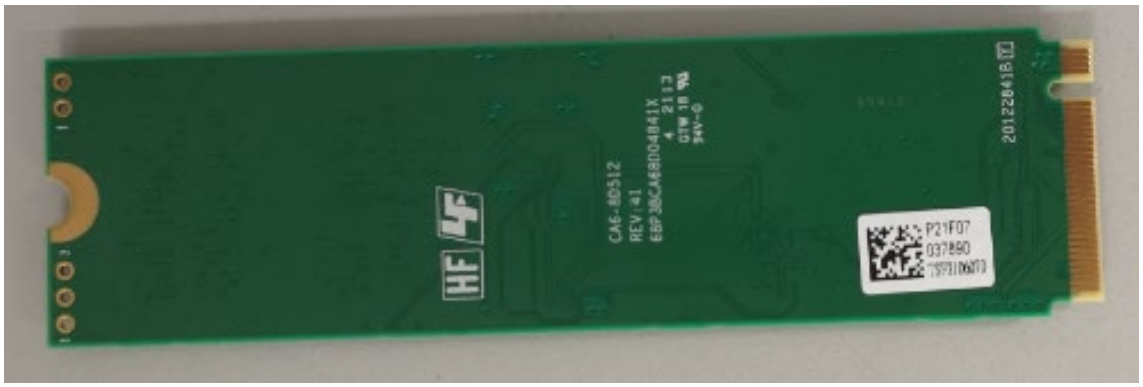


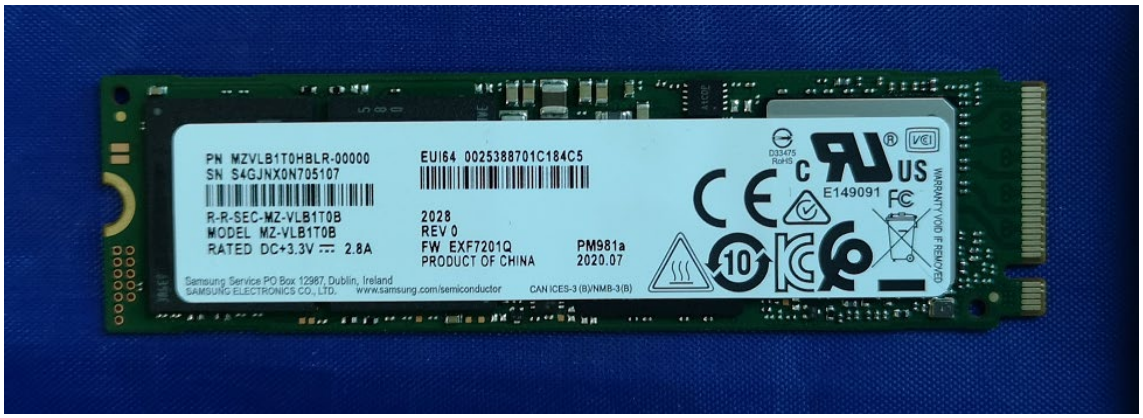

RC05-03500100-0000
TL140BDXP02-00
RoHS Made in China
TIANMA MICRO-ELECTRONIC CO LTD
XMT141125I120003W
EDID: 14

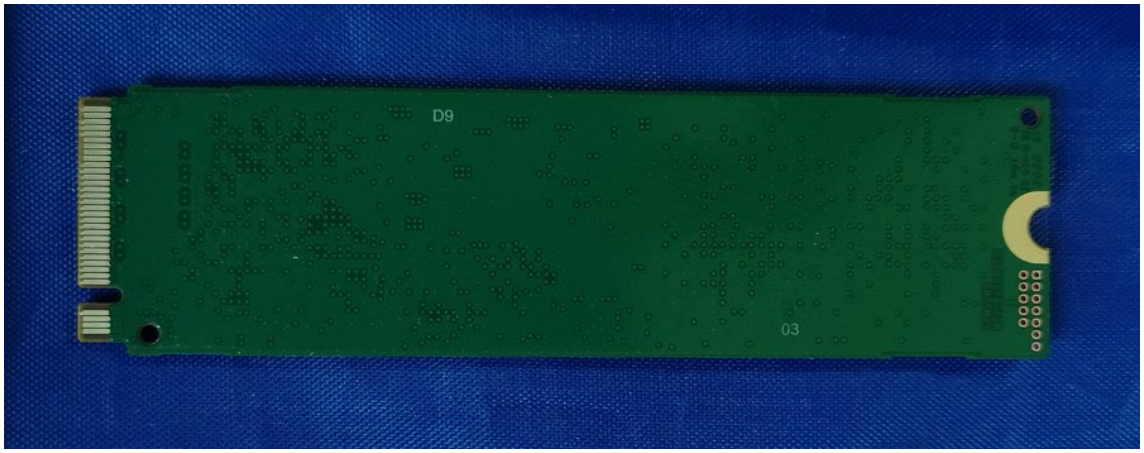

SOLID STATE STORAGE TECHNOLOGY CORPORATION
21F, 392, RUEY KUANG ROAD, NEIHU DIST., TAIPEI 114, Taiwan
Model: CA5-8D1024
S/N: 0020385000AA
R-R-PQX-CA5-8D1024
Power/電壓電流 : DC 3.3V 2.5A
https://www.ssstc.com
Solid State Drive / 固態硬碟
EUI: 38F60156-303485EC
Warranty Void If Label Removed
PN: 3C07180052
F/W: CQA0903
09/17/2020
PSID: FH4P13BM-H7AR37R6-
RMYZTUVD-50JMH7YD
D3D385
RoHS
E205203
MADE IN TAIWAN(台灣製造) 7224000456H-A MR-ML-02


BC
2009
94V-0 MRC
CA5-8D512
REV:21
68P3BCA58DXX521X
HF
19022721A
TP9
TP7 TP10


SOLID STATE STORAGE TECHNOLOGY CORPORATION
Model / 型號: CA6-8D1024
Solid State Drive / 固態硬碟
Power / 額定電壓 : +3.3V
S/N: 0021245001VA
P/N: 3C07180104
Capacity: 1024GB
F/W: ERA0901
06/18/2021
EUI: 38F60156-30B128E2
R-R-PQX-CA6-8D2048
CAN ICES-3(B)/ NMB-3(B)
https://www.ssstc.com
PSID:
HVR31VY3-97AGWM6J-
FJ4GQXXL-LPDM1HL0
WARRANTY VOID IF LABEL REMOVED
UK/EU Contacts:
KIOXIA Europe GmbH, Branch Office UK
31 Chertsey Street, Guildford, GU1 4HD, United Kingdom
KIOXIA Europe GmbH
Hansaallee 181, 40549 Düsseldorf, Germany
MADE IN TAIWAN 7224000505H-A MR-MXL-05

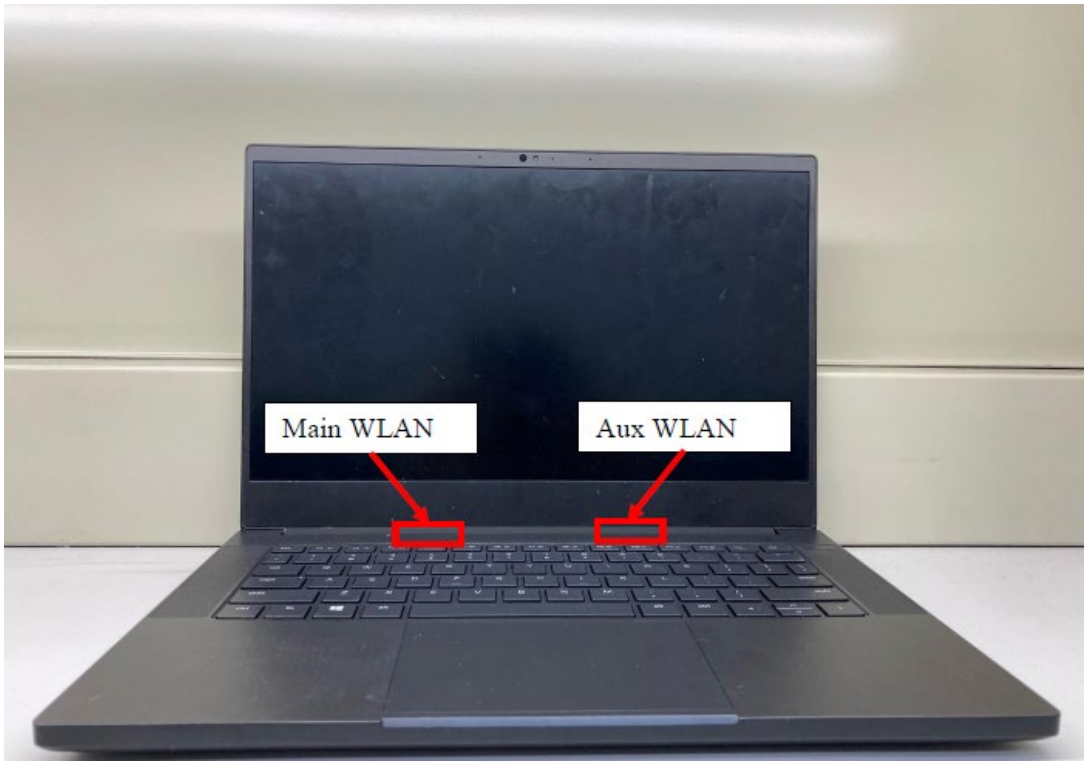

CA6-8D512
REV:41
P21F07


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MODEL MZ-VLB1T0B
RATED DC+3.3V 2.8A
EUI64 0025388701C184C5
2028
REV 0
FW EXF7201Q
PRODUCT OF CHINA
PM981a
2020.07
E149091
Samsung Service PO Box 12987, Dublin, Ireland
SAMSUNG ELECTRONICS CO., LTD.
www.samsung.com/semiconductor
CAN ICES-3 (B)/NMB-3(B)


D9
03


PM9A1 PRODUCT OF KOREA
1024GB REV 0
FW GXA7401Q
2131 2021.08
SN S676NE0R800920 R-R-SEC-MZ-VL21T00
EUI64 002538B811000416 MODEL MZ-VL21T00
PN MZVL21T0HCLR-00B00 RATED DC+3.3V 2.8A
PSID LUTYM1Q7REGUYUM7ESW15LCZQDP1AM1F
SAMSUNG ELECTRONICS CO., LTD.
www.samsung.com/semiconductor
CAN ICES-3 (B)/NMB-3(B)
WARRANTY VOID IF REMOVED


SAMSUNG
SSD


Main WLAN
Aux WLAN

